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Supplementary Materials for

Molecular-Scale Engineering of the Charge-Transfer Excited States in Non-Covalently Bound

Zn-Porphyrin and Carbon Fullerene based Donor-Acceptor Complex

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Table S1: Correspondence between HOMO and IP, and LUMO and EA calculated using OT-RSH/6-31G (d) for all monomers (PCBM, ZnPor, ZnChl and ZnBChl) and three D-A complexes (ZnPor@PCBM, ZnChl@PCBM and ZnBChl@PCBM). Electronic HOMO-LUMO gaps (ΔE_{H-L}) calculated using OT-RSH and B3LYP are also provided for comparison. All energies are in eV.

Systems	НОМО	IP	LUMO	EA	$\Delta \boldsymbol{E}_{\boldsymbol{H}-\boldsymbol{L}}$	
		(ΔSCF)		(ΔSCF)	B3LYP	OT-RSH
РСВМ	-7.3	-7.3	-2.0	-2.0	2.6	5.3
ZnPor	-6.6	-6.6	-1.0	-1.0	3.1	5.6
ZnChl	-6.2	-6.2	-1.0	-1.0	2.7	5.2
ZnBChl	-5.6	-5.6	-1.1	-1.1	2.1	4.5
ZnPor@PCBM	-6.3	-6.3	-2.0	-2.0	2.1	4.3
ZnChl@PCBM	-6.0	-6.0	-2.0	-2.0	1.7	4.0
ZnBChl@PCBM	-5.4	-5.4	-2.0	-2.0	1.2	3.4

Table S2: Low-lying Q-band, B-band and CT excited-electronic states for all monomers and three D-A complexes calculated in the gas-phase using TDDFT/OT-RSH. All energies are in eV. Oscillator strengths are listed within bracket. H and L stand for HOMO and LUMO, respectively. LE and CT indicate local and charge-transfer excitation, respectively. Percentage of significant MO configuration state function (CSF) for each excited-state is also provided.

System	Excitation	Important FMO	Nature of
	Energy	Contribution (%)	Electronic
			State
PCBM	2.3(0.0020)	H→L(92)	LE
	2.4(0.0000)	H→L+1(82)	LE
	2.4(0.0000)	H-2→L(69)	LE
	2.4(0.0000)	H-1→L(71)	LE

ZnPor	2.4 (0.0038)	H→L(36)	LE (Q)
		H-1→L+1(33)	
	2.4 (0.0038)	$H-1 \rightarrow L(33); H \rightarrow L+1(36)$	LE (Q)
	3.5 (0.0001)	H-2→L(99)	LE
	3.5 (0.0001)	H-2→L+1(99)	LE
	3.7(1.0126)	$H-1 \rightarrow L+1(48); H \rightarrow L(47)$	LE (B)
	3.7 (1.0131)	$H \rightarrow L+1(47); H-1 \rightarrow L(48)$	LE (B)
ZnChl	2.3(0.1294)	H→L(81)	LE(Q)
	2.6(0.0014)	H-1→L(57); H→L+1(41)	LE
	3.5(0.0003)	H-2→L(98)	LE
	3.7(0.9908)	H→L+1(57); H-1→L(39)	LE(B)
ZnBChl	1.9(0.2740)	H→L(94)	LE(Q)
	2.5(0.0411)	$H-1 \rightarrow L(71); H \rightarrow L+1(28)$	LE
	3.4(0.0002)	H-3→L(99)	LE
	3.6(0.0000)	H-2→L(97)	LE
	3.9(0.8161)	H→L+1(64)	LE(B)
	4.0(0.2523)	H-4→L(81)	LE
ZnPor@PCBM	2.1(0.0005)	$H \rightarrow L(34); H \rightarrow L+1(32); H-2 \rightarrow L(18)$	Partial CT
			[LE(A)+CT]
	2.2(0.0015)	H-2→ $L(37); H→L+1(31)$	Partial CT
			[LE(A)+CT]
	2.3(0.0007)	$H \rightarrow L+2(9); H-1 \rightarrow L(14); H-2 \rightarrow L(20)$	Partial CT
		H-4→L(10)	[LE(A)+CT]
	2.3(0.0002)	$H-1 \rightarrow L+1(33); H-2 \rightarrow L+1(24)$	Partial CT
			[LE(A)+CT]
	2.3(0.0002)	$H-1 \rightarrow L(14); H-2 \rightarrow L+1(18)$	Partial CT
		H-3→L(44)	[LE(A)+CT]
	2.3(0.0003)	H→L+2(22); H-4→L(42)	Partial CT
			[LE(A)+CT]
	2.3(0.0001)	$H-1 \rightarrow L+1(17); H-2 \rightarrow L+1(24)$	Partial CT
		H-3→L(30)	[LE(A)+CT]
	2.4(0.0020)	$H \rightarrow L(16); H \rightarrow L+2(37); H-4 \rightarrow L(13)$	Partial CT
			[LE(A)+CT]
	2.4(0.0010)	H-1→L+2(19); H-1→L+3(13)	Q+CT

		H-1→L+4(13)	
	2.4(0.0004)	$H \rightarrow L+3(5); H \rightarrow L+4(31); H-1 \rightarrow L+3(27)$	Q
	3.4(0.1625)	H→L+4(15); H-1→L+3(16)	В
	3.4(0.2334)	$H \rightarrow L+3(11); H \rightarrow L+4(13);$	В
		H-1→L+3(15); H-1→L+4(11)	
ZnChl@PCBM	1.9 (0.0007)	$H \rightarrow L$ (38); $H \rightarrow L+1$ (53); $H \rightarrow L+5$ (5)	СТ
	2.0 (0.0004)	$H \rightarrow L (37); H \rightarrow L+1 (31); H \rightarrow L+2 (26)$	СТ
	2.1 (0.0020)	$H \rightarrow L (11); H \rightarrow L+2 (39)$	СТ
		H-1→L (13); H-1→L+1 (17)	
	2.1 (0.0008)	$H \rightarrow L$ (8); $H \rightarrow L+2$ (27); $H-1 \rightarrow L$ (17)	СТ
		H-1→L+1 (24); H-2→L (9)	
	2.2 (0.0023)	H-1→L+1 (26)	Partial CT
		H-2→L(40)	[LE(A) + CT]
	2.3 (0.0008)	H-1→L (19); H-1→L+2 (23)	Partial CT
		H-2→L (28)	[LE(A) + CT]
	2.3 (0.0042)	H-2→L+1 (46); H-3→L (23)	LE (A)
	2.3 (0.0532)	H→L+3 (50); H-1→L+2 (10)	Q
		H-1→L+6 (10); H-2→L+1 (10)	
	3.5 (0.1958)	$H \rightarrow L+6 (35); H-1 \rightarrow L+3 (14)$	CT + B
ZnBChl@PCBM	1.3 (0.0006)	$H \rightarrow L (33); H \rightarrow L+1 (60); H \rightarrow L+5 (5)$	СТ
	1.4 (0.0002)	H→L (48); H→L+1 (26)	Partial CT
		H→L+2 (22)	[L.E(D) + CT]
	1.5 (0.0005)	$H \rightarrow L (17); H \rightarrow L+1 (8)$	Partial CT
		H→L+2 (71)	[L.E(D) + CT]
	2.0 (0.1497)	H→L+3 (81)	Q
	3.9 (0.0842)	$\text{H-9} \rightarrow \text{L+3 (14); H} \rightarrow \text{L+9 (8)}$	CT + B

Table S3: Gas-phase exciton binding (E_{xb}) energies for the lowest-excited CT state (CT_1) for all three D-A complexes calculated using B3LYP and OT-RSH functionals.

D-A Complex	E_{xb} (eV)				
	B3LYP	OT-RSH			
ZnPor@PCBM	0.4	2.2			
ZnChl@PCBM	0.4	2.1			
ZnBChl@PCBM	0.4	2.1			

D-A Complex	<i>S</i> ₁		Q-band		B-band	
	B3LYP	OT-RSH	B3LYP	OT-RSH	B3LYP	OT-RSH
PCBM	1.9	2.3	-	-	-	-
ZnPor	2.4	2.4	2.4	2.4	3.5	3.7
ZnChl	2.4	2.3	2.4	2.3	3.6	3.7
ZnBChl	2.0	1.9	2.1	1.9	3.8	3.9
ZnPor@PCBM	1.7	2.1	2.4	2.4	3.1	3.4
ZnChl@PCBM	1.3	1.9	2.3	2.3	3.1	3.5
ZnBChl@PCBM	0.8	1.3	2.0	2.0	4.0	3.9

Table S4: Comparison of gas-phase excited-state energies (the lowest-excited S_1 , Q and B-band electronic states) for all monomers and D-A complexes calculated using B3LYP and OT-RSH functionals. All energies are in eV.

Table S5: Calculated solvation energies considering both partial and full charge-separation (CS) for the lowest CT state (*i.e.*, CT_1) in polar solvent DMF. Reorganization energies (λ_i) obtained from DFT and CDFT methods considering a full CS are also listed for comparison. All energies are in eV.

D-A Complex	Solvation	Energy	λ_i		
	Partial CS Full CS		DFT	CDFT	
ZnPor@PCBM	0.05	0.45	0.143	0.234	
ZnChl@PCBM	0.30	0.40	0.142	0.210	
ZnBChl@PCBM	0.29	0.40	0.139	0.158	

Table S6: Calculated reorganization energy for the D-A complex (λ_i) using CDFT optimized CTstate geometry and for the solvent (λ_s) using modified Marcus two-sphere model considering both partial and full charge-separation (CS) for the lowest CT electronic-state (*i.e.*, *CT*₁) in polar solvent DMF. All energies are in eV.

D-A Complex	λ_i		λ_s		
	Partial Full		Partial	Full	
	CS	CS	CS	CS	
ZnPor@PCBM	0.064	0.234	0.132	0.527	
ZnChl@PCBM	0.176	0.210	0.428	0.528	
ZnBChl@PCBM	0.131	0.158	0.432	0.534	

Table S7: Calculated electronic couplings (V_{el}) , driving forces (ΔE), activation energy (E_a) for CT in DMF, and also total reorganization energy ($\lambda_r = \lambda_i + \lambda_s$) considering CDFT-optimized CT geometry for estimating λ_i , and the Marcus forward (k_f) and backward (k_b) CT rates (in s⁻¹) calculated at 298 K considering CT-state associated with partial (values without bracket) and full CS (values within bracket). All energies are in eV.

D-A Complex	V _{el}	ΔΕ	λ_r	E _a	CT Rate		
					k _f	k _b	$\frac{\mathbf{k}_f}{\mathbf{k}_b}$
ZnPor@PCBM	0.012	0.414	0.196	0.061	5.1×10^{11}	5.1×10^{4}	1.0×10^{7}
		(0.984)	(0.761)	(0.016)	(1.5×10^{12})	(3.3×10^{-5})	(4.5×10^{16})
ZnChl@PCBM	0.035	0.876	0.604	0.031	8.0×10^{12}	1.2×10^{-2}	6.7×10^{14}
		(1.010)	(0.738)	(0.025)	(9.0×10^{12})	(7.5×10^{-5})	(1.2×10^{17})
ZnBChl@PCBM	0.026	1.121	0.563	0.138	6.9×10^{10}	7.6×10^{-9}	9.1 × 10 ¹⁸
		(1.258)	(0.692)	(0.116)	(1.5×10^{11})	(8.0×10^{-11})	(1.9×10^{21})



Figure S1: Non-covalent interactions (NCI) plots for all three D-A complexes. Blue, green and red coloured iso-surfaces indicate the strong, weak and repulsive interactions, respectively. An iso-value of 0.004 e/Å^3 is used. D-A interfacial green coloured iso-surfaces clearly suggest the presence of weak non-covalent dispersion interactions.



Figure S2: FMOs iso-surfaces for all monomers (isolated donors and acceptor) calculated using OT-RSH/6-31G (d). HOMO and LUMO energies are also listed in eV.



Figure S3: Localization of quasi-electron (yellow) and quasi-hole (cyan) densities in the lowest CT excited-state (*i.e.*, CT_1) for the three D-A complexes calculated using OT-RSH/6-31G (d). An iso-value of 0.0005 e/Å³ is used to plot these density iso-surfaces.